

## General Description

The MY70P06D uses P-Channel MOSFET uses advanced trench technology and design to provide excellent RDS(on) with low gate charge. It can be used in a wide variety of applications.

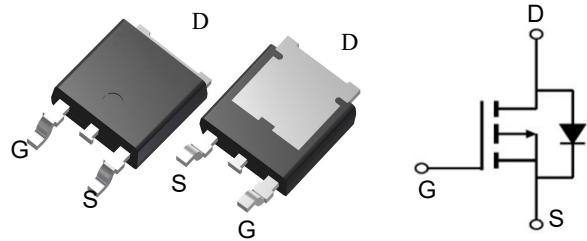


## Features

X <sub>FUU</sub>	-60	X
K <sub>F</sub>	-70	C
T <sub>FUQP+CVXI U?-10X+</sub>	16.5	o á
T <sub>FUQP+CVXI U?-4.5X+</sub>	18.5	o á

## Application

- Battery protection
- Load switch
- Uninterruptible power supply



## Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
MY70P06D	TO-252	MY70P06D	2500

## Absolute Maximum Ratings (T<sub>c</sub>=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	-60	V
V <sub>GS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub> @T <sub>c</sub> =25°C	Continuous Drain Current, V <sub>GS</sub> @ -10V <sup>1,6</sup>	-70	A
I <sub>D</sub> @T <sub>c</sub> =100°C	Continuous Drain Current, V <sub>GS</sub> @ -10V <sup>1,6</sup>	-60	A
I <sub>DM</sub>	Pulsed Drain Current <sup>2</sup>	-280	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	700	mJ
P <sub>D</sub> @T <sub>c</sub> =25°C	Total Power Dissipation <sup>4</sup>	270	W
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	°C
T <sub>J</sub>	Operating Junction Temperature Range	-55 to 150	°C
R <sub>θJC</sub>	Thermal Resistance Junction-case <sup>1</sup>	0.46	°C/W

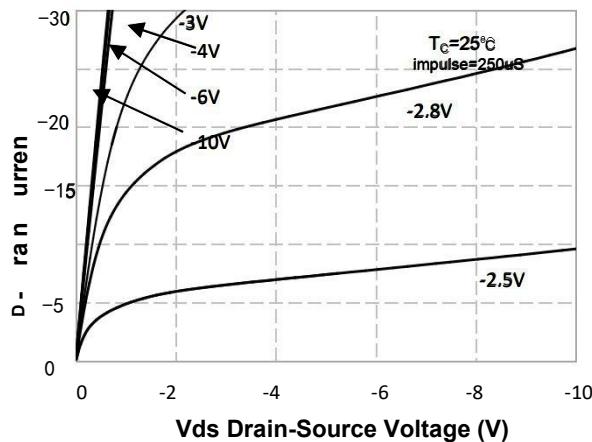
**Electrical Characteristics ( $T_J=25^\circ C$ , unless otherwise noted)**

Symbol	Parameter	Conditions	Min	Typ	Max	Units
<b>Off Characteristics</b>						
<b><math>BV_{DSS}</math></b>	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250 \mu A$	-60	---	---	V
<b><math>I_{DSS}</math></b>	Zero Gate Voltage Drain Current	$V_{GS}=0V, V_{DS}=-60V$	---	---	-1	$\mu A$
<b><math>I_{GSS}</math></b>	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0A$	---	---	$\pm 100$	nA
<b>On Characteristics</b>						
<b><math>V_{GS(th)}</math></b>	GATE-Source Threshold Voltage	$V_{GS}=V_{DS}, I_D=-250 \mu A$	-1.1	-1.6	-2.2	V
<b><math>R_{DS(on)}</math></b>	Static Drain-Source On-Resistance	$V_{GS}=-10V, I_D=-20A$	---	16.5	20	$m\Omega$
		$V_{GS}=-4.5V, I_D=-20A$	---	18.5	22	
<b>Dynamic Characteristics</b>						
<b><math>C_{iss}</math></b>	Input Capacitance	$V_{DS}=-20V, V_{GS}=0V, f=1MHz$	---	4399	---	pF
<b><math>C_{oss}</math></b>	Output Capacitance		---	258	---	
<b><math>C_{rss}</math></b>	Reverse Transfer Capacitance		---	211	---	
<b>Switching Characteristics</b>						
<b><math>t_{d(on)}</math></b>	Turn-On Delay Time	$V_{DD}=-30V, I_D=-20A,$ $V_{GS}=-10V, R_G=1\Omega$	---	23	---	ns
<b><math>t_r</math></b>	Rise Time		---	17	---	ns
<b><math>t_{d(off)}</math></b>	Turn-Off Delay Time		---	55	---	ns
<b><math>t_f</math></b>	Fall Time		---	29	---	ns
<b><math>Q_g</math></b>	Total Gate Charge	$V_{GS}=-10V, V_{DS}=-30V,$ $I_D=-20A$	---	114	---	nC
<b><math>Q_{gs}</math></b>	Gate-Source Charge		---	27.3	---	nC
<b><math>Q_{gd}</math></b>	Gate-Drain "Miller" Charge		---	49	---	nC
<b>Drain-Source Diode Characteristics</b>						
<b><math>V_{SD}</math></b>	Drain Diode Forward Voltage	$V_{GS}=0V, I_S=-20A$	---	---	-1.2	V
<b><math>I_s</math></b>	Continuous Source Current	$V_G=V_D=0V$	---	---	-70	A
<b><math>I_{SM}</math></b>	Pulsed Source Current		---	---	-280	A
<b><math>T_{rr}</math></b>	Reverse Recovery Time	$T_J = 25^\circ C, IF = -20A,$ $di/dt = 100A/\mu s$	---	117	---	nS
<b><math>Q_{rr}</math></b>	Reverse Recovery Charge		---	420	---	nC

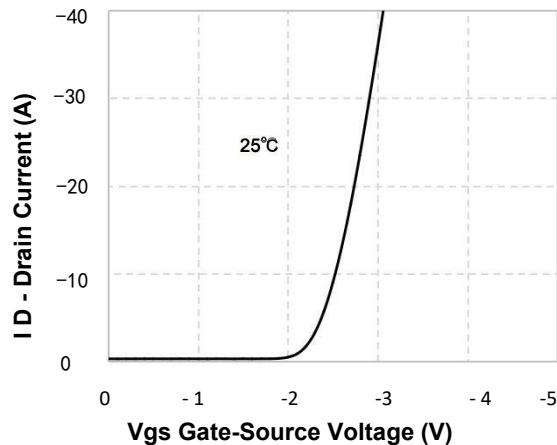
**Notes:**

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
2. EAS condition:  $T_J = 25^\circ\text{C}$ ,  $V_{DD} = -25\text{V}$ ,  $V_G = -5\text{V}$ ,  $R_G = 25\Omega$ ,  $L = 0.5\text{mH}$ ,  $I_{AS}$
3. Pulse Test: Pulse Width  $\leq 300\mu\text{s}$ , Duty Cycle  $\leq 0.5\%$

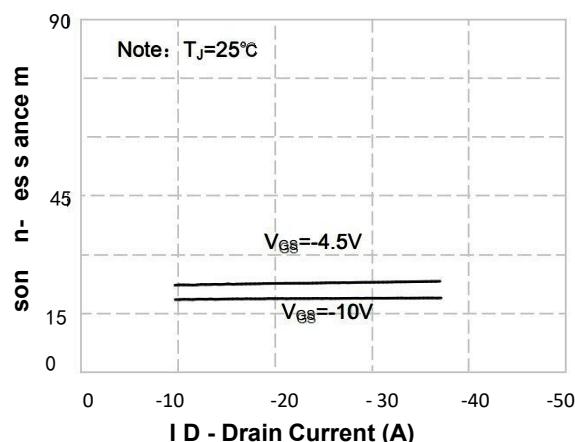
**Typical Characteristics:** ( $T_c=25^\circ\text{C}$  unless otherwise noted)



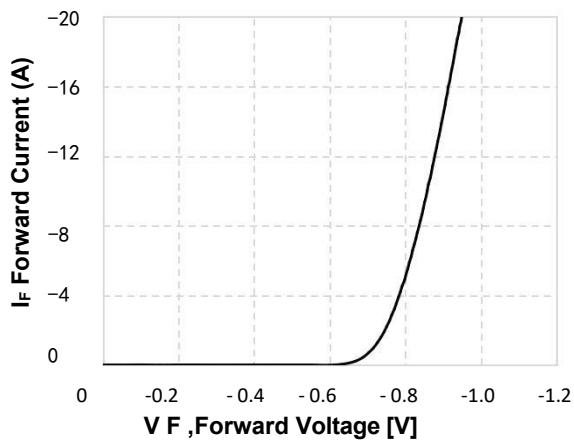
**Figure 1. On-Region Characteristics**



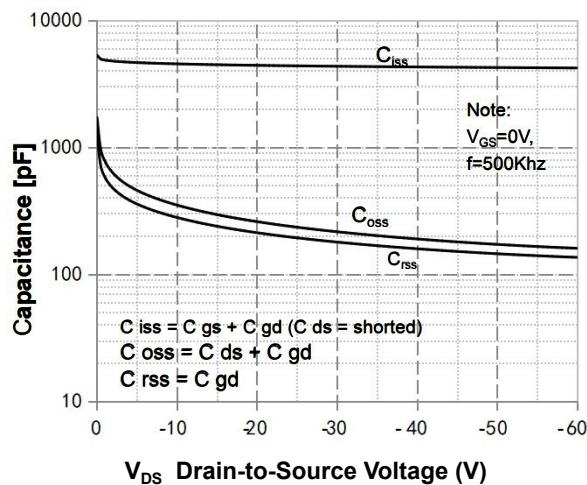
**Figure 2. Transfer Characteristics**



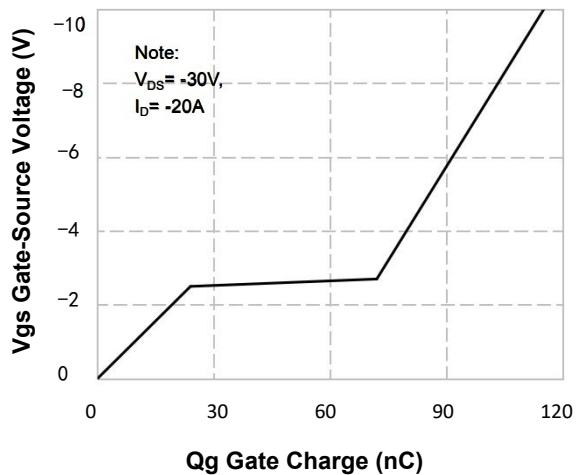
**Figure 3. On-Resistance Variation vs  
Drain Current and Gate Voltage**



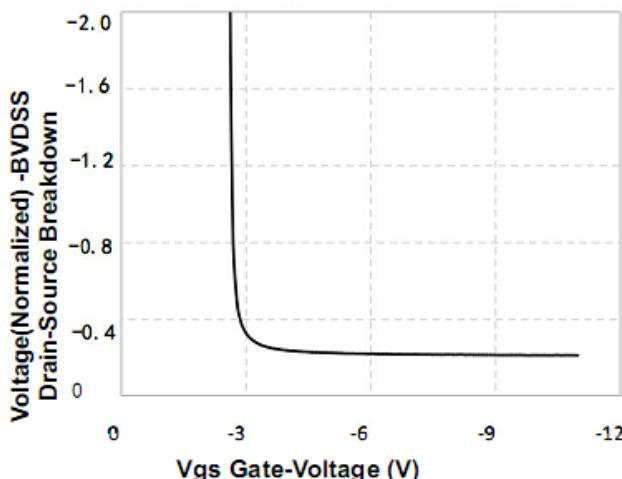
**Figure 4. Body Diode Forward Voltage  
Variation with Source Current  
and Temperature**



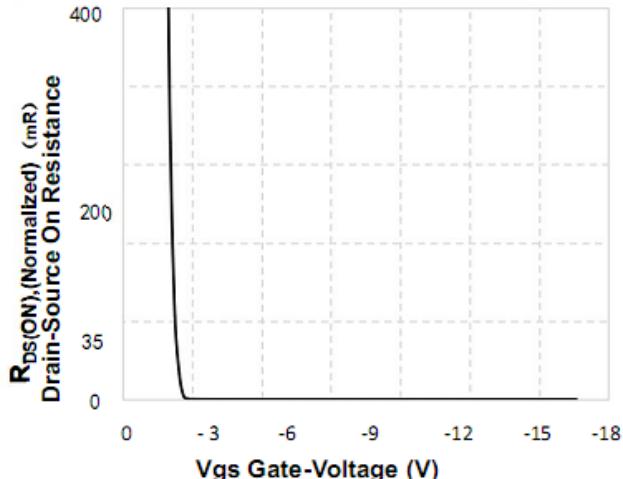
**Figure 5. Capacitance Characteristics**



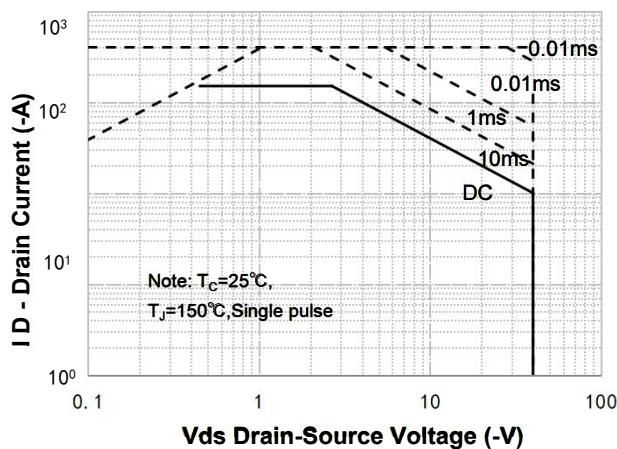
**Figure 6. Gate Charge Characteristics**



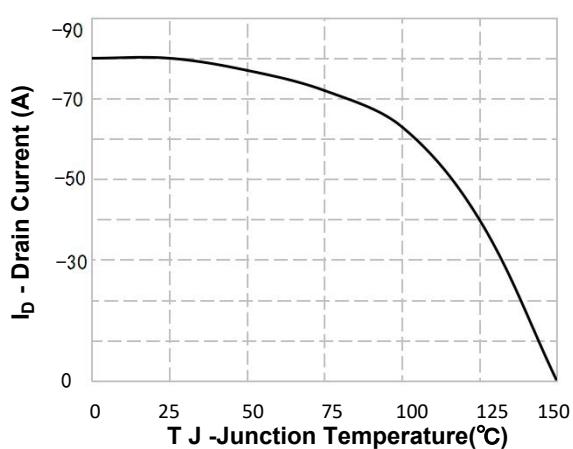
**Figure 7. Breakdown Voltage Variation vs Gate-Voltage**



**Figure 8. On-Resistance Variation vs Gate Voltage**

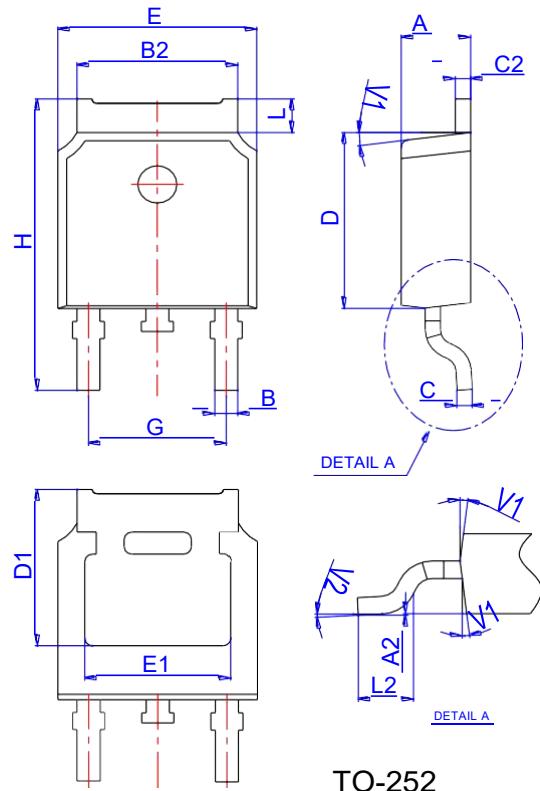


**Figure 9. Maximum Safe Operating Area**



**Figure 10. Maximum Continuous Drain Current vs Case Temperature**

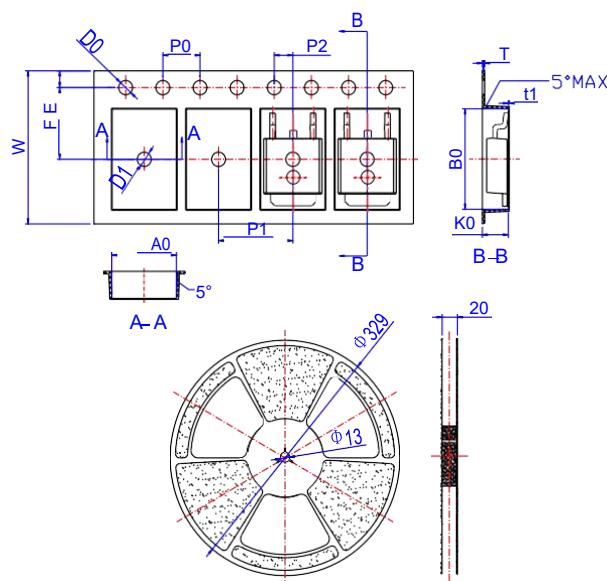
**Package Mechanical Data-TO-252-JQ Single**



TO-252

Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	2.10		2.50	0.083		0.098
A2	0		0.10	0		0.004
B	0.66		0.86	0.026		0.034
B2	5.18		5.48	0.202		0.216
C	0.40		0.60	0.016		0.024
C2	0.44		0.58	0.017		0.023
D	5.90		6.30	0.232		0.248
D1	5.30REF			0.209REF		
E	6.40		6.80	0.252		0.268
E1	4.63			0.182		
G	4.47		4.67	0.176		0.184
H	9.50		10.70	0.374		0.421
L	1.09		1.21	0.043		0.048
L2	1.35		1.65	0.053		0.065
V1		7°			7°	
V2	0°		6°	0°		6°

**Reel Specification-TO-252**



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
W	15.90	16.00	16.10	0.626	0.630	0.634
E	1.65	1.75	1.85	0.065	0.069	0.073
F	7.40	7.50	7.60	0.291	0.295	0.299
D0	1.40	1.50	1.60	0.055	0.059	0.063
D1	1.40	1.50	1.60	0.055	0.059	0.063
P0	3.90	4.00	4.10	0.154	0.157	0.161
P1	7.90	8.00	8.10	0.311	0.315	0.319
P2	1.90	2.00	2.10	0.075	0.079	0.083
A0	6.85	6.90	7.00	0.270	0.271	0.276
B0	10.45	10.50	10.60	0.411	0.413	0.417
K0	2.68	2.78	2.88	0.105	0.109	0.113
T	0.24		0.27	0.009		0.011
t1	0.10			0.004		
10P0	39.80	40.00	40.20	1.567	1.575	1.583